

RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/986,332

a total area covered by said second selective growth mask is larger than an area of said first selective growth mask; and

Bread said first selective growth mask and said second selective growth mask are positioned such that a combination of said first selective growth mask and said second selective growth mask is over or covers a total surface area of said underlayer.

Please add the following new claims:

189. (New) A method according to claim 1, wherein said dissimilar substrate is made of a material selected from the group consisting of sapphire, SiC, MgAl₂O₄, ZnS, GaAS, and Si.

190. (New) A method according to claim 1, wherein said first selective growth mask is made of a material selected from the group consisting of silicon oxide (SiO_x), silicon nitride (Si_xN_y), titanium oxide (TiO_x), and zirconium oxide (ZrO_x).

B2 191. (New) A method according to claim 1, wherein said first selective growth mask is a multilayer film comprising materials selected from the group consisting of silicon oxide (SiO_x), silicon nitride (Si_xN_y), titanium oxide (TiO_x), and zirconium oxide (ZrO_x).

192. (New) A method according to claim 1, wherein said first selective growth mask is a multilayer film comprising silicon oxide (SiO₂)/titanium oxide (TiO_x).

RESPONSE TO RESTRICTION REQUIREMENT and
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U.S. Application No. 09/986,332

193. (New) A method according to claim 1, wherein said nitride semiconductor is made of $\text{In}_a\text{Al}_b\text{Ga}_{1-a-b}\text{N}$, wherein $0 \leq a$, $0 \leq b$, and $a + b \leq 1$.

194. (New) A method according to claim 1, wherein said nitride semiconductor is made of GaN.

195. (New) A method according to claim 1, wherein the nitride semiconductor has crystal defects of not more than $1 \times 10^5/\text{cm}^2$ at the first major surface thereof.

196. (New) A method according to claim 1, wherein said nitride semiconductor portions are grown to a thickness of $5 \mu\text{m}$ or more.

197. (New) A method according to claim 1, further comprising a step (c) of removing at least said support member from said nitride semiconductor portions.

198. (New) A method according to claim 48, wherein said dissimilar substrate is made of a material selected from the group consisting of sapphire, SiC, MgAl_2O_4 , ZnS, GaAS, and Si.

199. (New) A method according to claim 48, wherein said second selective growth mask is made of a material selected from the group consisting of silicon oxide (SiO_x), silicon nitride (Si_xN_y), titanium oxide (TiO_x), and zirconium oxide (ZrO_x).

RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/986,332

200. (New) A method according to claim 48, wherein said second selective growth mask is a multilayer film comprising materials selected from the group consisting of silicon oxide (SiO_x), silicon nitride (Si_xN_y), titanium oxide (TiO_x), and zirconium oxide (ZrO_x).

201. (New) A method according to claim 48, wherein said second selective growth mask is a multilayer film comprising silicon oxide (SiO_2)/titanium oxide (TiO_x).

202. (New) A method according to claim 48, wherein said first selective growth mask and said second selective growth mask are formed of SiO_2

203. (New) A method according to claim 48, wherein said second nitride portions are made of GaN.

204. (New) A method according to claim 48, wherein said second selective growth mask is positioned to cover regions of said nitride semiconductor portions corresponding to said plurality of first windows of said first selective growth mask.

205. (New) A method according to claim 204, wherein said second nitride semiconductor portions have fewer crystal defects than said first semiconductor portions.

RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/986,332

206. (New) A method according to claim 48, wherein said first selective growth mask and said second selective growth mask are both 0.1 μm thick.

B2 end
207. (New) A method according to claim 48, further comprising a step (e) of removing at least said support member from said second nitride semiconductor portions.
